Silicon NPN Power Transistors 2N6326 2N6327 2N6328

DESCRIPTION

- With TO-3 package
- Low collector saturation voltage
- High DC current gain

APPLICATIONS

- Designed for audio amplifier and switching circuits applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N6326	Open emitter	60	V
		2N6327		80	
		2N6328		100	
V_{CEO}	Collector-emitter voltage	2N6326	Open base	60	V
		2N6327		80	
		2N6328		100	
V_{EBO}	Emitter-base voltage		Open collector	5	V
I_C	Collector current			30	A
I_B	Base current			7.5	A
P_D	Total power dissipation		T_C=25℃	200	W
T_j	Junction temperature			200	℃
T_{stg}	Storage temperature			-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}c}$	Thermal resistance junction to case	0.875	℃/W

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	2N6326	I_C=0.2 A ;I_B=0	60			V
		2N6327		80			
		2N6328		100			
V_{CEsat}	Collector-emitter saturation voltage		I_C=15A; I_B=1.5A			1.2	V
V_{BEsat}	Base-emitter saturation voltage		I_C=15A; I_B=1.5A			1.5	V
V_{BE}	Base-emitter on voltage		I_C=8A ; V_{CE}=4V			1.5	V
I_{CBO}	Collector cut-off current	2N6326	V_{CB}=60V; I_E=0 T_C=150℃			1.0 5.0	mA
		2N6327	V_{CB}=80V; I_E=0 T_C=150℃			1.0 5.0	
		2N6328	V_{CB}=100V; I_E=0 T_C=150℃			1.0 5.0	
I_{EBO}	Emitter cut-off current		V_{EB}=4V; I_C=0			1.0	mA
h_{FE-1}	DC current gain		I_C=8A ; V_{CE}=4V	25			
h_{FE-2}	DC current gain		I_C=30A ; V_{CE}=4V	6		30	
f_T	Transition frequency		I_C=1A ; V_{CE}=10V;f=1.0MHz	3			MHz

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PACKAGE OUTLINE

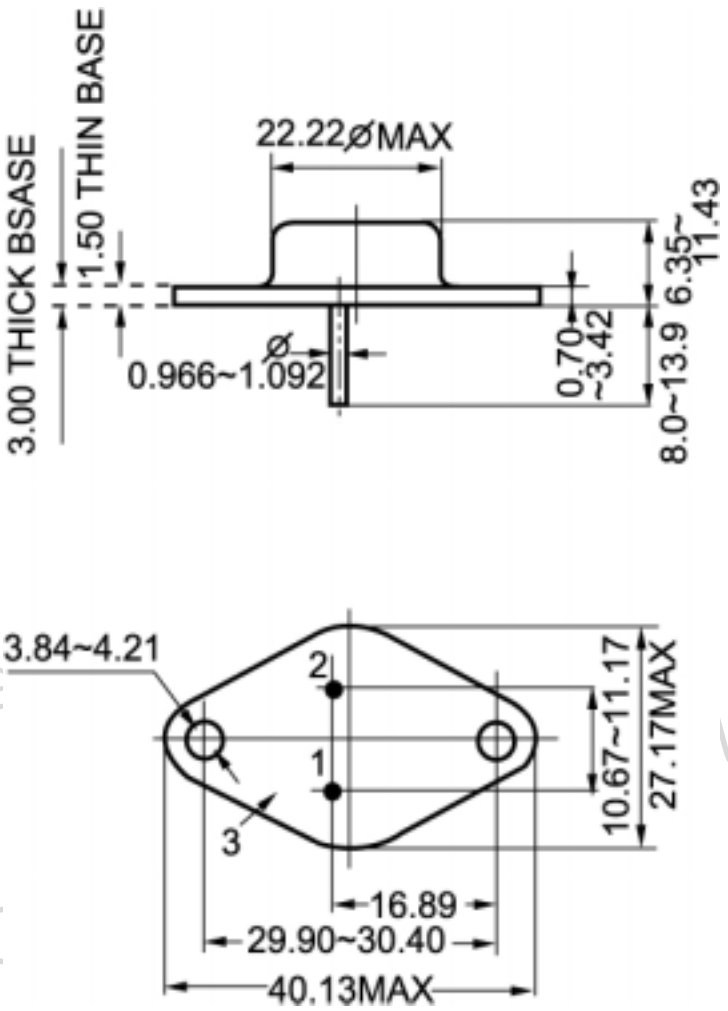

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)